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Gate control of Berry phase in semiconductor quantum dots

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Berry phase in semiconductor quantum dots (QDs) can be induced by moving the dots adiabatically in a closed loop with the application of the distortion potential in the lateral direction. We show that the Berry phase is highly sensitive to the electric fields arising from the interplay between the Rashba and the Dresselhaus spin-orbit couplings. We report that the accumulated Berry phase can be induced from other available quantum state that are only differed by one quantum number of the same spin state. The sign change in the g-factor due to the penetration of the Bloch wavefunctions into the barrier material can be reflected in the Berry phase. We solve the time dependent Schrödinger equation and investigate the evolution of the spin dynamics during the adiabatic movement of the QDs in the 2D plane. Our results might open the possibilities of building a topological quantum dot quantum computer where the Berry phase can be engineered and can be manipulated with the application of the spin-orbit couplings through gate controlled electric fields.

I. INTRODUCTION

Manipulating the single electron spins in QDs through the non-Abelean geometric phases has attracted considerable attention since the pioneering work of Berry.[1–6] For a system of degenerate quantum states, Wilczek and Zee showed that the geometric phase factor is replaced by a non-Abelian time dependent unitary operator acting on the initial states within the subspace of degeneracy.[7,8] Since then the geometric phase has been measured experimentally for a variety of systems such as quantum states driven by a microwave field[9] and qubits with tilted magnetic fields.[10,11] Manipulation of the spin qubits through the Berry phase implies that the injected data can be read out with different phase that can be topologically protected from the outside world.[12–20] Several recent reviews of the Berry phase have been presented in Refs. 21 and 22. One of the promising research proposals for building a solid state topological quantum computer is that the accumulated Berry phase in QD system can be manipulated with the interplay between the Rashba-Dresselhaus spin-orbit couplings.[1,16] The Rashba spin-orbit coupling arises from the asymmetric triangular quantum well along the growth direction and the Dresselhaus spin-orbit coupling arises due to bulk inversion asymmetry in the crystal lattice.[23,24] A recent work by Bason et.al shows that the Berry phases can be measured for a two level quantum system in a superadiabatic basis comprising the Bose-Einstein condensates in optical lattices.[25]

Recently, it has been shown that the geometric phase can be induced on the electron spin states in QDs by moving the dots adiabatically in a closed loop in the 2D plane with the application of gate controlled electric field.[8,17] Furthermore, the authors in Refs. 26–28 have recently proposed to build a QD device in the absence of the magnetic fields that can perform the quantum gate operations (NOT gate, Hadamard gate and Phase gate) with the application of the externally applied gate potential modulated by a sinusoidal varying potential. In this paper, we transport the electron spin states in QDs in presence of the externally applied magnetic fields along z-direction in a closed loop in the 2D plane with the application of time dependent distortion potential. We investigate the interplay between the Rashba and the Dreeselhaus spin-orbit couplings on the scalar Berry phase.[3,29] The transport of the dots is carried out very slowly so that the adiabatic theorem can be applied on the evolution of the spin dynamics. In particular, the sign change in the g-factor of electrons in the QDs due to the penetration of the Bloch wavefunctions into the barrier materials can be manipulated with the interplay between the Rashba-Dresselhaus spin-orbit couplings in the Berry phase. We show that the Berry phase in QDs can be engineered and can be manipulated with the application of the spin-orbit couplings through gate controlled electric fields. We solve the time dependent Schrödinger equation and investigate the evolution of spin dynamics in QDs.

II. THEORETICAL MODEL

From the two band Kane model, the Hamiltonian of an electron in QDs in the plane of a 2 Dimensional Electron Gas (2DEG) in the presence of an external magnetic field B, along the z-direction in III-V semiconductor QDs can be written as[30,31]

$$H = H_{xy} + H_R + H_D, \tag{1}$$

where the Hamiltonians H_R and H_D are associated with the Rashba and the Dresselhaus spin-orbit couplings and H_{xy} is the Hamiltonian of the electron along the lateral direction in the plane of the 2DEG. H_{xy} can be written as

$$H_{xy} = \frac{\vec{P}^2}{2m} + \frac{1}{2} m\omega_o^2 (x^2 + y^2) + f(t) + \frac{\hbar}{2}\omega_z \sigma_z, \tag{2}$$

where $\vec{P} = \vec{p} + e\vec{A}$ is the kinetic momentum operator, $\vec{p} = -i\hbar(\partial_x, \partial_y, 0)$ is the canonical momentum operator and $\vec{A}$ is the vector potential in the symmetric gauge, $\omega_z = g_0\mu_B B/\hbar$ is the Zeeman frequency and g_0 is the bulk g-factor. Here, $-e < 0$ is the electronic charge, m is the effective mass of the electron in the conduction band, μ_B is the Bohr magneton, σ_z is the Pauli spin matrix along z-direction. Also, $\omega_0 = \frac{\hbar}{m\ell_0^2}$ is a parameter characterizing the strength of the confining potential and ℓ_0 is the radius of the QD. The time dependent function $f(t)$ is the distortion potential that can be used to let the dot to move adiabatically in a closed loop in the 2D plane without disturbing the spin splitting energy difference. We use the functional form of $f(t)$ in our theoretical model as[3]

$$f(t) = eF_x(t)x + eF_y(t)y, \tag{3}$$

where $F_x = f_0\cos(\omega t)$, $F_y = f_0\sin(\omega t)$, f_0 is the amplitude and ωt varies from 0 to 2π.

The Hamiltonian H_{xy} can be exactly diagonalized[31] by considering the gauge potential in the form of $\vec{A} = \frac{B}{2}\left((-y+\bar{y}_0),(x+\bar{x}_0),0\right)$, where $\bar{x}_0 = eF_x(t)/(m\omega_o^2)$, $\bar{y}_0 = eF_y(t)/(m\omega_o^2)$ and the energy spectrum of H_{xy} can be written in terms of number operators $n_\pm = a_\pm^\dagger a_\pm$ as

$$H_{xy} = \left(n_+ + \frac{1}{2}\right)\hbar\omega_+ + \left(n_- + \frac{1}{2}\right)\hbar\omega_- - G + \frac{\hbar}{2}\omega_z\sigma_z, \tag{4}$$

$$a_\pm = \frac{\ell}{2\hbar}\left(ip_x \pm p_y\right) + \frac{1}{2\ell}\left[(x+\bar{x}_0) \mp i\left(y+\bar{y}_0\right)\right], \tag{5}$$

$$a_\pm^\dagger = \frac{\ell}{2\hbar}\left(-ip_x \pm p_y\right) + \frac{1}{2\ell}\left[(x+\bar{x}_0) \pm i\left(y+\bar{y}_0\right)\right], \tag{6}$$

provided that $\left[a_\pm, a_\pm^\dagger\right] = 1$. Here $\omega_\pm = \Omega \pm \omega_c/2$, $\Omega = \sqrt{\omega_0^2 + \frac{1}{4}\omega_c^2}$, $\omega_c = \frac{eB}{m}$ is the cyclotron frequency, $\ell = \sqrt{\hbar/(m\Omega)}$ is the hybrid orbital length and $G = \frac{1}{2}\left(eF_x(t)\bar{x}_0 + eF_y(t)\bar{y}_0\right)$.

The Hamiltonians associated with the Rashba-Dresselhaus spin-orbit couplings can be written as[23,24]

$$H_R = \frac{\alpha_R}{\hbar}\left(\sigma_x P_y - \sigma_y P_x\right), \tag{7}$$

$$H_D = \frac{\alpha_D}{\hbar}\left(-\sigma_x P_x + \sigma_y P_y\right). \tag{8}$$

The strength of the Rashba-Dresselhaus spin-orbit couplings is characterized by the parameters α_R and α_D which are given by

$$\alpha_R = \gamma_R eE, \qquad \alpha_D = 0.78\gamma_D\left(\frac{2me}{\hbar^2}\right)^{2/3}E^{2/3}. \tag{9}$$

The Rashba and Dresselhaus spin-orbit Hamiltonians can be written in terms of raising and lowering operators as:[31]

$$H_R = \alpha_R\left(\xi_+\sigma_+a_+ - \xi_-\sigma_-a_-\right) + H.c. + \frac{\alpha_R eB}{2\hbar}\left(\sigma_x\bar{x}_0 + \sigma_y\bar{y}_0\right), \tag{10}$$

$$H_D = i\alpha_D\left(\xi_+\sigma_-a_+ + \xi_-\sigma_+a_-\right) + H.c. + \frac{\alpha_D eB}{2\hbar}\left(\sigma_x\bar{y}_0 + \sigma_y\bar{x}_0\right), \tag{11}$$

where $\xi_\pm = \frac{1}{\ell} \pm \frac{eB\ell}{2\hbar}$, $\sigma_\pm = \frac{\sigma_x \pm \sigma_y}{2}$ and $H.c.$ represents the Hermitian conjugate.

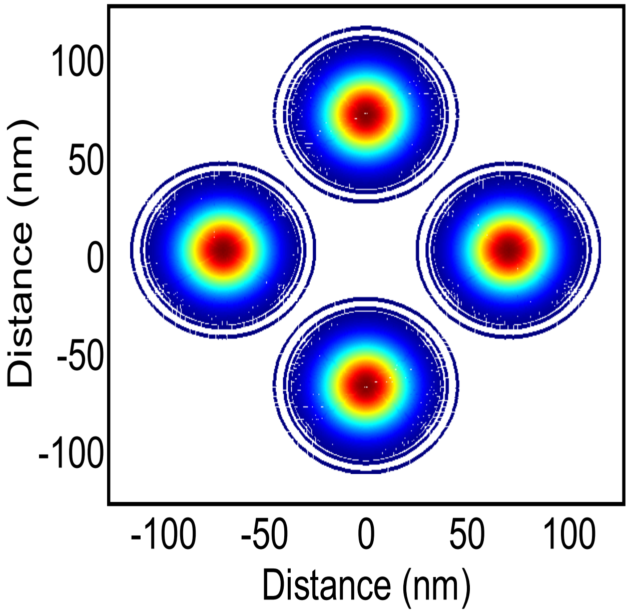

FIG. 1. (Color online) Contour plots of the realistic electron wave function in GaAs QDs that are adiabatically transported in one complete rotation in the plane of 2DEG (see Ref. 17) under the influence of externally applied gate potential. We choose the amplitude $f_0 = 5\times10^3$ V/cm, electric field $E = 10^5$ V/cm, $B = 1$T and QD radius $\ell_0 = 20$ nm. The energy difference between the spin states are reported as $\varepsilon_{0,0,-1/2} - \varepsilon_{0,0,+1/2} = 0.025$ meV, and $\varepsilon_{0,1,-1/2} - \varepsilon_{0,0,-1/2} = 2.1$ meV which is constant during the adiabatic transport of the QDs.

We now turn to the calculation of the Berry phase in QDs. According to works of Berry, if parameters contained in the Hamiltonian of a quantal system are adiabatically carried around a closed loop, an extra geometric phase (Berry phase) is induced in addition to the familiar dynamical phase.[6,32] A slow variation of such parameters along a closed path C will return the system to its original energy eigenstate with an additional phase factor $\exp\{i\gamma_n(C)\}$. More specifically, the state acquires phases after a period of the cycle T as

$$|\Psi_n(T)\rangle = \exp\left\{-\frac{i}{\hbar}\int_0^T \varepsilon_n(t)\,dt\right\}\cdot\exp\left\{i\gamma_n(C)\right\}\,|\psi_n\rangle, \tag{12}$$

where the coefficients $\gamma_n(C)$ can be written as

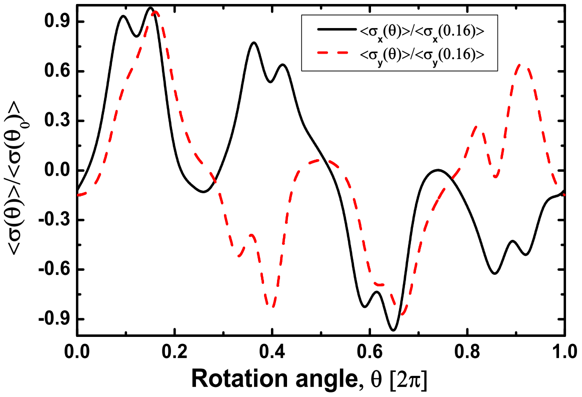

FIG. 2. (Color online) Evolution of spin dynamics during the adiabatic transport of the GaAs quantum dots. We chose $E = 5 \times 10^5\ V/cm$ and the rest of the parameters are chosen as the same as in Fig. 1.

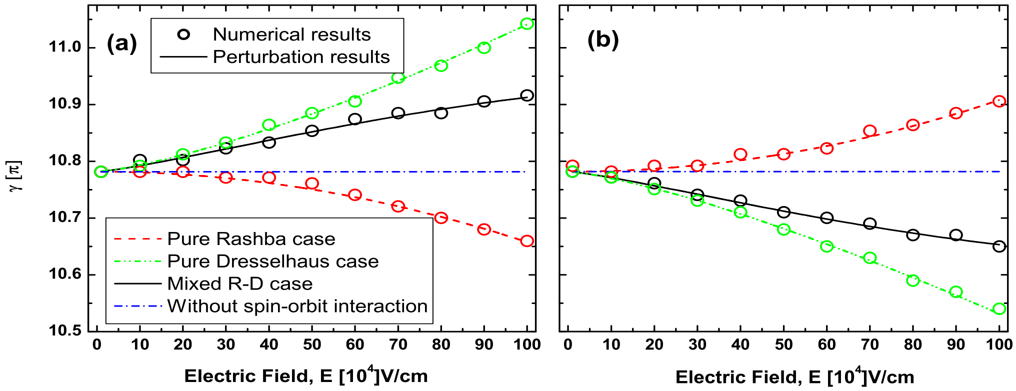

FIG. 3. (Color online) Contributions of the Rashba-Dresselhaus spin-orbit couplings to the Berry phase induced on the spin state $|0,0,+1/2>$ in Fig. 2(a) and on the spin state $|0,0,-1/2>$ in Fig. 2(b) in GaAs QDs. Due to different symmetry orientations in the crystal lattice, the contributions of the Rashba (dashed lines) and the Dresselhaus (dashed-dotted-dotted lines) spin orbit couplings to the Berry phase diverge from the Zeeman value in QDs. The parameters are chosen the same as in Fig. 1.

$$\gamma_n(C) = -i \oint_C d\mathbf{s} \sum_{m \neq n} \frac{< n|\boldsymbol{\nabla}_{\boldsymbol{R}} \nabla_R \hat{H}(\mathbf{R})|m > \times < m|\boldsymbol{\nabla}_{\boldsymbol{R}} \hat{H}(\mathbf{R})|n >}{(\varepsilon_m(\mathbf{R}) - \varepsilon_n(\mathbf{R}))^2}, \tag{13}$$

where $\mathbf{R} = (F_x(t), F_y(t))$ and $d\mathbf{s}$ is the total area enclosed by the dots in one complete adiabatic rotation in the 2D plane at the heterojunction. Since, we are interested in calculating the accumulated Berry phase in the lowest Landau levels, we consider $m = 0, 0, \pm 1/2$ and investigate the contribution to the Berry phase from the higher energy states in the QD system. As it is clear from Eq. 13, the Berry phase can be induced from the higher energy states differed by one quantum number of the same spin states if we consider the distortion potential as an adiabatic control parameter (see Eq. 2). It means, we need to consider $n = 0, 1, \pm 1/2$. Other choices of the parameters such as $n = 1, 0, \pm 1/2$ also induce a non-Berry phase which is comparatively very small. Based on the second

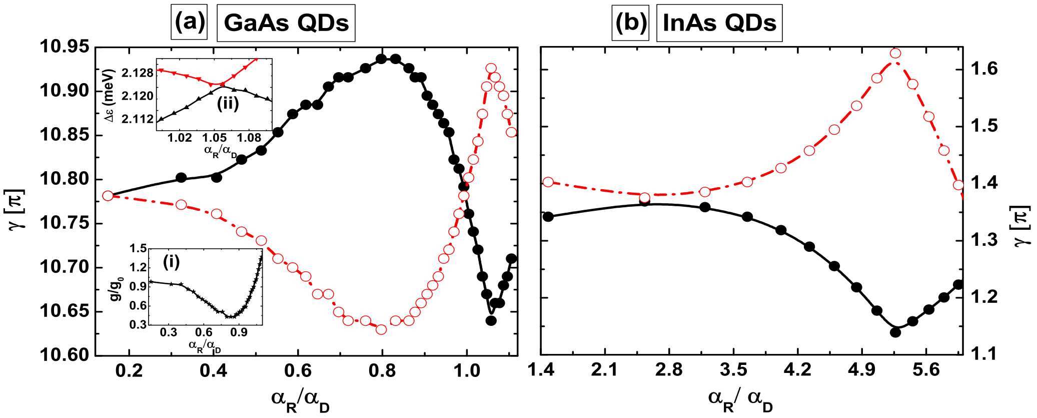

FIG. 4. (Color online) Berry phase (absolute value) induced on the spin state $|0,0,+1/2>$ (solid lines, circle) and $|0,0,-1/2>$ (dashed-dotted line, square) in QDs. Inset plot (i) shows the energy difference $(\varepsilon_{0,1,+1/2}-\varepsilon_{0,0,-1/2}$ (triangle pointing down)) and $(\varepsilon_{0,1,-1/2}-\varepsilon_{0,0,-1/2}$(triangle pointing up)) vs ratio of α_R to α_D. Inset plot (ii) shows the variation of the g-factor $(g=\left(\varepsilon_{0,1,+1/2}-\varepsilon_{0,0,-1/2}\right)/(\mu_B B))$ in QDs. The parameters are chosen as same as Fig. 1.

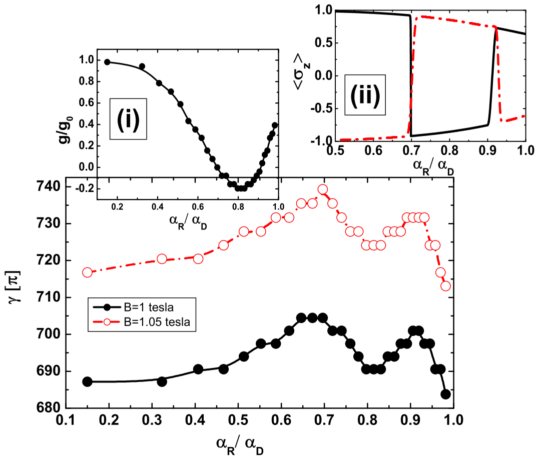

FIG. 5. (Color online) Berry phase (absolute value) induced on the spin state $|0,0,+1/2>$ in GaAs QDs. First maximum in the Berry phase can be seen due to the fact that the g-factor of electron changes its sign (see inset plot (i)). The parameters are chosen the same as in Fig. 1 but $\ell_0 = 35\ nm$. Inset plot (ii) shows the expectation value of σ_z for the states $|0,0,-1/2>$ (solid line) and for the states $|0,0,+1/2>$ (dashed-dotted line).

order perturbation theory, Eq. 13 can be written as

$$\gamma_{0,0,+1/2} = \frac{-e^2\ell^2}{\left[\hbar\omega_- + \xi_-^2\left(\frac{\alpha_R^2}{\varrho_+} - \frac{\alpha_D^2}{\varrho_-}\right)\right]^2}\oint_C d\mathbf{s}, \quad (14)$$

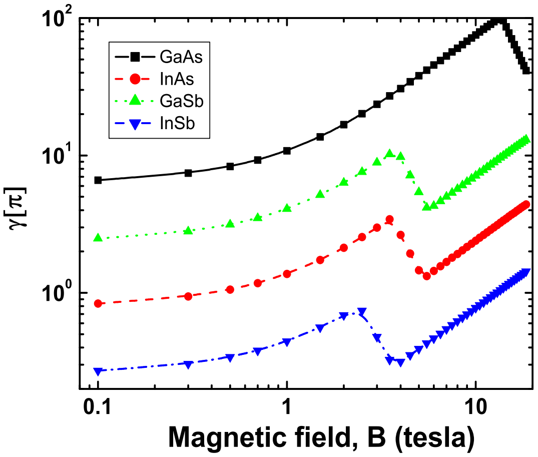

FIG. 6. (Color online) Berry phase (absolute value) induced on the spin state $|0,0,+1/2>$ vs longitudinal magnetic field in III-V semiconductor QDs. Here we choose $E = 3\times10^5\ V/cm$ and $\ell_0 = 20\ nm$. Notice that the Berry phase terminates at the crossing point.

$$\gamma_{0,0,-1/2} = \frac{-e^2\ell^2}{\left[\hbar\omega_- - \xi_-^2\left(\frac{\alpha_R^2}{\varrho_+} - \frac{\alpha_D^2}{\varrho_-}\right)\right]^2}\oint_C d\mathbf{s}, \quad (15)$$

where $\varrho_\pm = \hbar\omega_- \pm \Delta$ and $\Delta = g_0\mu_B B$. The negative sign in Eqs. 14 and 15 shows that, after one complete adiabatic rotation of the dots, the Berry phase is pointed into the plane of the 2DEG. It can be seen that the Berry phase is highly sensitive to the QD radius, magnetic fields and the strength of the Rashba-Dresselhaus spin-orbit coupling.

III. RESULTS AND DISCUSSIONS

We have used the Finite Element Method (FEM)[30] and perturbation theory to solve the corresponding eigenvalue problem with Hamiltonian given by Eq. (1) to study the control of single electron spins through the Berry phase in III-V semiconductor QDs.

In Fig. 1, we use the distortion potential ($f(t)$) as a time dependent function and allow the dot to move adiabatically in a closed loop in the 2D plane. Realistic electron wavefunctions of the dots at different locations ($\theta = 0, \pi/2, \pi, 3\pi/2$) in the 2D plane are shown. The total adiabatic area enclosed by the dots in the 2D plane is $d\mathbf{s} = \pi d^2/4 \approx 7.8 \times 10^{-7}\mathrm{eV}^2/\mathrm{nm}^2$. The material constants for GaAs, InAs, GaSb and InSb semiconductors are taken from Ref. 33.

Based on FEM,[34] we solved the time dependent Schrödinger equation with Hamiltonian $H(x, y, \theta)$ and the initial condition $H(x, y, 0)\psi(x, y, 0) = \varepsilon\psi(x, y, 0)$ at the fixed time interval $\theta = [0 : 0.1 : 2\pi]$. The adiabatic theorem guarantee that $\psi^{'}_{\theta}(x, y, \theta) = 0$. We plotted the evolution of the spin dynamics during the adiabatic movement of the QDs in the 2D plane in Fig. 2. Even in the presence of Zeeman energy, where the magnetic field is applied along z-direction, the spin components in the ground state of the QDs are not well defined due to the presence of spin-orbit couplings.[27,28] It means, $< \sigma_z >$ is either 1 or -1 (depending on the g-factor of electron in QDs; see inset plot of Fig. 5(ii)) and the components of $\sigma_i (i = x, y)$ varies during the adiabatic movement of the QDs in the 2D plane. Fluctuations in $< \sigma_z >$ can be made at degenerate sublevels where the effective Land*é* g-factor exactly vanishes. In this case, rather than finding a scalar Berry phase, one needs to find the matrix Berry phase acting on the initial states within the subspace of degeneracy.[8] Since the motivation of the paper is to investigate the influence of electric and magnetic fields on the scalar Berry phase, we choose the parameters in Fig. 2 in such a way that the g-factor is negative and $< \sigma_z >= +1$.[30] If one choses $\ell_0 = 40\ nm$, it can be found that the g-factor is $+ve$ and $< \sigma_z >= -1$. Since the periodicity of the propagating waves is different for the pure Rashba and for the pure Dresselhaus case, we see the superposition effect in the x- and y-components of the electron spin in QDs (see Fig. 2).

We now turn to the key results of the paper: the analysis of the Berry phase accumulated during the adiabatic transport of the dots in the 2D plane.

In Fig. 3, we study the contributions of the Rashba-Dresselhaus spin-orbit couplings to the Berry phase on the spin states $|0, 0, +1/2>$ (Fig. 3(a)) and $|0, 0, -1/2>$ (Fig. 3(b)) in GaAs QDs. We see that the Berry phase for the pure Rashba (dashed line) and the pure Dresselhaus (dashed-dotted-dotted line) cases diverges from the Zeeman value (dashed-dotted line) due to the interplay between the different symmetry orientations in the dots (see Eq. 17). In the range of $E = (1 - 100) \times 10^4$ V/cm, from Eq. 9, it can be seen that $\alpha_R/\alpha_D < 1$ for GaAs QDs. It means that only the Dresselhaus spin-orbit coupling has an appreciable contribution in the manipulation of the Berry phase in QDs.

In Fig. 4(a), the abrupt changes (i.e. the first maximum or minimum) in the tunability of the Berry phase at $\alpha_R/\alpha_D \approx 0.8$ can be seen due to the fact that the Bloch wavefunctions can be pushed near the edge of the barrier materials but still resides in the QD region because the Land*é* $g-$factor of electron is still negative (see intet plot, Fig. 4(a)(i)). Second maximum or minimum in the Berry phase at $\alpha_R/\alpha_D \approx 1.15$ can be seen due to the level crossing between the states $|0, 1, -1/2>$ and $|0, 1, +1/2>$ (see inset plot Fig. 4(a)(ii)). The second maximum or minimum point can be exactly found from the condition $\varepsilon_{0,1,+1/2} = \varepsilon_{0,1,-1/2}$ and is given by

$$\Delta - \alpha_D^2 \left[\frac{3\xi_-^2}{\varrho_-} - \frac{\xi_+^2}{\eta_+}\right] = -\alpha_R^2 \left[\frac{3\xi_-^2}{\varrho_+} - \frac{\xi_+^2}{\eta_-}\right], \qquad (16)$$

where $\eta_\pm = \hbar\omega_+ \pm \Delta$. From condition (16), it is clear that the crossing point in the Berry phase is highly sensitive to the magnetic fields, QD radius and the Rashba-Dresselhaus spin-orbit couplings. The interplay between the Rashba-Dresselhaus spin-orbit couplings with the Zeeman spin splitting energy determine the exact location of the second maximum or minimum point. In Fig. 4(b), we study the Berry phase in InAs QDs. Similar to GaAs, the level crossing in the Berry phase can be seen at $\alpha_R/\alpha_D = 5.2$.

Let us consider the quantitative difference between the Berry phase accumulated on the electron spin states $|0, 0, \pm1/2>$. For simplicity, we only consider the second power of the Rashba-Dresseselhaus spin-orbit coupling:

$$\sqrt{\frac{\gamma_{0,0,+1/2}}{\gamma_{0,0,-1/2}}} = 1 - \frac{2m}{\hbar^3\Omega}\left[\alpha_R^2\left(1 - \frac{\Delta}{\hbar\omega_-}\right) - \alpha_D^2\left(1 + \frac{\Delta}{\hbar\omega_-}\right)\right]. \qquad (17)$$

In InAs and InSb QDs, the Rashba spin-orbit coupling coefficients are larger than the Dresselhaus spin-orbit coupling coefficients. It means, the Berry phase accumulated on the spin states $|0, 0, -1/2>$ is greater than the phase accumulated on the spin states $|0, 0, +1/2>$. However, for GaAs and GaSb QDs, the Dresselhaus spin-orbit coupling dominates which produces the greater Berry phase on the spin states $|0, 0, +1/2>$. However at large values of the gate controlled electric fields along z-direction, the Rashba spin-orbit coupling dominates and we find the larger Berry phase on the spin states $|0, 0, -1/2>$ (see the Berry phase at $\alpha_R/\alpha_D > 1$ in Fig. 4(a)).

In Fig. 5, we investigate the interplay between Rashba-Dresselhaus spin-orbit couplings on the Berry phase accumulated during the adiabatic transport of the quantum dots in the 2D plane at different magnetic fields ($B = 1\ T$ (solid lines) and $B = 1.05\ T$ (dashed-dotted lines)). Here we see that the large enhancement in the Berry phase occurs with very small increment in the magnetic fields. This indicates that the Berry phase is highly sensitive to the magnetic fields in QDs. The first maximum (approx. $\alpha_R/\alpha_D = 0.67$) in the Berry phase can be seen due to the sign change in the g-factor of electrons in QDs (see inset plot). It means, the Bloch wavefunction starts to penetrate into the barrier materials. Experimentally, the penetration of the Bloch wavefunction in AlGaAs/GaAs heterojunction can be engineered with the application of the gate controlled electric fields along the z-direction where the bulk g-factor of electron for GaAs material is negative, and for AlGaAs it is positive.[35] Second maximum at $\alpha_R/\alpha_D = 0.9$ can be seen due to the fact that the wavefunctions of electron are pushed back into the GaAs material. The minimum point (i.e., at $\alpha_R/\alpha_D = 0.9$) in the Berry phase and in the g-factor indicates that the Bloch wavefunction are getting pushed towards the QD region due to the interplay between the Rashba and the Dresselhaus spin-orbit couplings. In the inset plot Fig. 5 (ii), the sign change in the g-factor can be reflected in $< \sigma_z >$ at $\alpha_R/\alpha_D = 0.67$ and 0.9. Fig. 6 investigates the Berry phase vs magnetic fields in III-V semiconductor QDs. It can be seen that the level crossing in the Berry phase can be achieved with the accessible values of the magnetic fields in QDs.

Finally, let us give the experimental realization of the measurement of the Berry phase in III-V semiconductor QDs. Even though the distortion potential does not affect the spin splitting energy difference in the QDs, several parameters such as $F_x(t)$, $F_y(t)$ and θ in the distortion potential can relate to the other control parameters, α_R, α_D, ω_0, and ω_z of the dots, so that one can experimentally realize the adiabatic movement of the QDs in the 2D plane. Following Refs. 3, 9, 10, and 25, the adiabatic movement of the dots can be performed by choosing the frequency ω of the microwave pulse in a fraction of $\varepsilon^0_{0,0,\pm1/2}/\hbar$ and ω_0. Also, the amplitude of the pulse $F_x(t)$ and $F_y(t)$ (see Eq. 3) can be chosen in a fraction of the electric fields (see Eq. 9) to study the interplay between the Rashba and the Dresselhaus spin-orbit couplings on the Berry phase in QDs.

To conclude, we have calculated the evolution of the spin dynamics (and the superposition due to the Rashba-Dresselhaus spin-orbit couplings can be seen) during the adiabatic movement of the QDs in the 2D plane. We have shown that the Berry phase in the lowest Landau levels of the QDs can be generated from the higher quantum states that are only differed by one quantum number of the same spin states. The Berry phase is highly sensitive to the magnetic fields, QD radius and the Rashba-Dresselhaus spin-orbit coupling coefficients. Our theoretical predictions of the manipulation of the Berry phase can be utilized to engineer devices where the semiconductor QDs are adiabatically transported with the realistic experimental parameters. We have also provided the theoretical condition for the experimental realization of the measurement of the Berry phase in QDs. In this case, the read out quantum spin states in the Berry phase are topologically protected that can help in building a topological solid state quantum computer. We have shown that the sign change in the g-factor in the Berry phase can be manipulated with the interplay between the Rashba and the Dresselhaus spin-orbit couplings.

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